

### 2N6727 TRANSISTOR (PNP)

#### FEATURES

Power dissipation

$$P_{CM} : 1 \text{ W (Tamb=25°C)}$$

Collector current

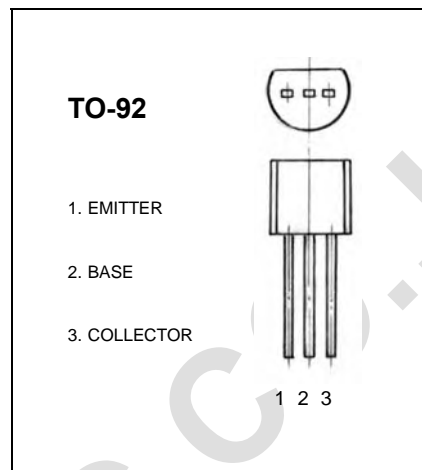
$$I_{CM} : -1.5 \text{ A}$$

Collector-base voltage

$$V_{(BR)CBO} : -50 \text{ V}$$

Operating and storage junction temperature range

$$T_J, T_{stg} : -55°C \text{ to } +150°C$$



#### ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1 \text{ mA}, I_E = 0$	-50			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -10 \text{ mA}, I_B = 0$	-40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1 \text{ mA}, I_C = 0$	-5			V
Collector cut-off current	$I_{CBO}$	$V_{CB} = -50 \text{ V}, I_E = 0$			-0.1	$\mu\text{A}$
Collector cut-off current	$I_{CEO}$	$V_{CB} = -40 \text{ V}, I_B = 0$			-1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = -5 \text{ V}, I_C = 0$			-0.1	$\mu\text{A}$
DC current gain	$H_{FE(1)}$	$V_{CE} = -1 \text{ V}, I_C = -1 \text{ A}$	50		250	
	$H_{FE(2)}$	$V_{CE} = -1 \text{ V}, I_C = -10 \text{ mA}$	55			
	$H_{FE(3)}$	$V_{CE} = -1 \text{ V}, I_C = -100 \text{ mA}$	60			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -1 \text{ A}, I_B = -100 \text{ mA}$			-0.5	V
Base-emitter voltage	$V_{BE(on)}$	$V_{CE} = -1 \text{ V}, I_C = -1 \text{ A}$			-1.2	V
Transition frequency	$f_T$	$V_{CE} = -10 \text{ V}, I_C = -50 \text{ mA}$	50			MHz